

HCRZ120N40M2A

N-Channel SiC Silicon Carbide Power MOSFET

1200 V, 57 A, 40 mΩ

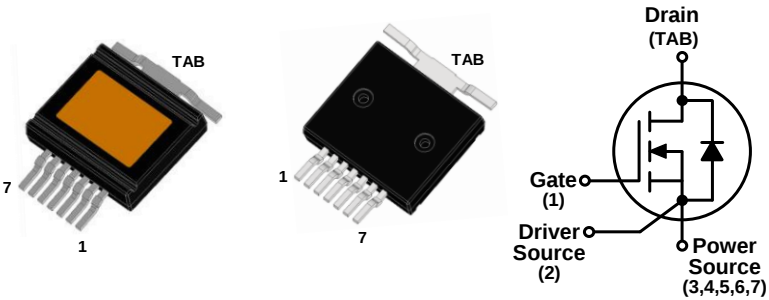
Features

- High switching speed with a low gate charge
- Isolated substrate / High dielectric strength
- Isolation rating of 3.6kVrms
- 100% Avalanche Tested
- Pb-free, Halogen Free, and RoHS Compliant
- AEC Q101 Qualified

$BV_{DSS}, T_c=25^{\circ}C$	$I_D, T_c=25^{\circ}C$	$R_{DS(on),typ}$	$Q_{g,typ}$
1200 V	57 A	40 mΩ	62 nC

Benefits

- Top-side-cooling package
- Longer clearance / creepage distance
- Kelvin source connection
- Higher frequency applicability
- Easy heatsink assembly with thermal grease



Applications

- Automotive applications (OBC, e-Comp, DC/DC)
- Solar inverter
- EV charging station
- UPS, Industrial power supply



Absolute Maximum Ratings ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		1200	V
V_{GS}	Gate to Source Voltage (DC)		-10 / +22	V
V_{GSop}	Recommended Operation Value		-5...-3 / +18	V
I_D	Drain Current	Continuous ($T_C = 25^{\circ}C$)	57	A
		Continuous ($T_C = 100^{\circ}C$)	40	
I_{DM}	Drain Current	Pulsed (Note1)	142	A
P_D	Power Dissipation	($T_C = 25^{\circ}C$)	156	W
		Derate Above 25°C	1.9	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 175	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		260	°C

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.96	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
HCRZ120N40M2A	HCRZ120N40M2A	TO-263-7L V2 (DBC)	Tape and Reel	700 units

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$		1	100	μA
		$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175^\circ\text{C}$		10		
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = +22\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
		$V_{GS} = -10\text{ V}, V_{DS} = 0\text{ V}$			-100	

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10\text{ mA}$ (tested after $V_{GS} = 22\text{ V}, 1\text{ ms pulse}$)	2.0	3.0	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 18\text{ V}, I_D = 28\text{ A}$		40.0	54.0	m Ω
		$V_{GS} = 18\text{ V}, I_D = 28\text{ A}, T_J = 175^\circ\text{C}$		64.0		
		$V_{GS} = 15\text{ V}, I_D = 28\text{ A}$		55.5		
g_{fs}	Transconductance	$V_{DS} = 20\text{ V}, I_D = 28\text{ A}$		16.9		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$		1668		pF
C_{oss}	Output Capacitance			105		
C_{rss}	Reverse Capacitance			4		
E_{oss}	Stored Energy in Output Capacitance	$V_{DS} = 0\text{ V to } 800\text{ V}, V_{GS} = 0\text{ V}$		42		μJ
$C_{o(er)}$	Energy Related Output Capacitance			132		pF
$C_{o(tr)}$	Time Related Output Capacitance			201		
$Q_{g(tot)}$	Total Gate Charge	$V_{DS} = 800\text{ V}, I_D = 28\text{ A},$ $V_{GS} = -3\text{ V} / 18\text{ V},$ Inductive load		62		nC
Q_{gs}	Gate to Source Charge			20		
Q_{gd}	Gate to Drain "Miller" Charge			14		
R_G	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 30\text{ mV}$		3.0		Ω

Switching Characteristics

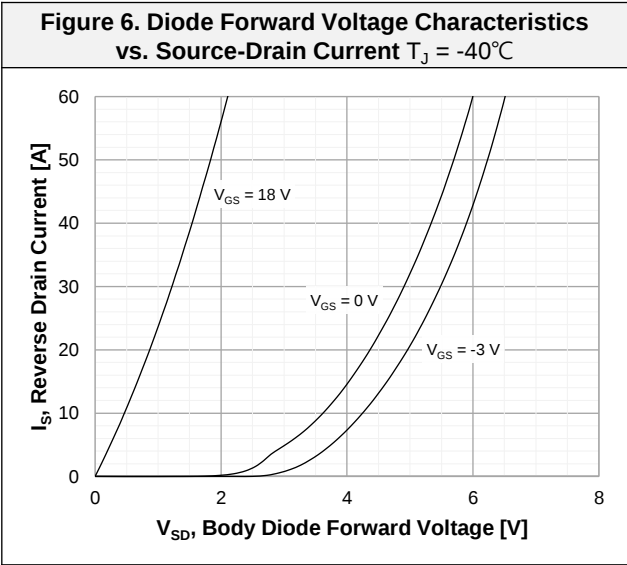
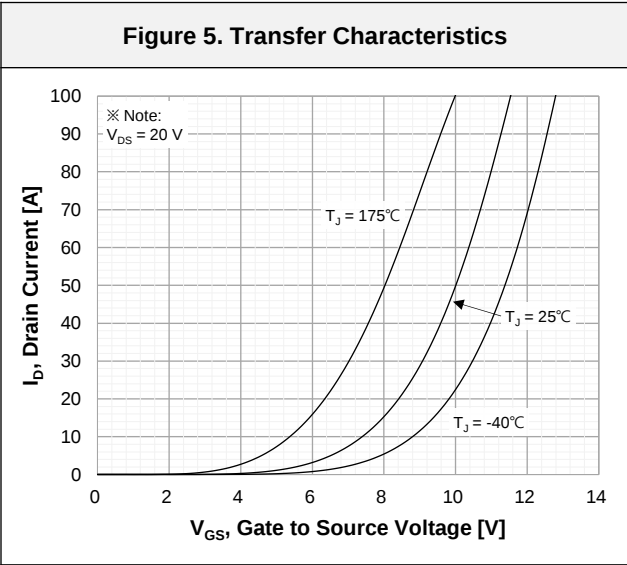
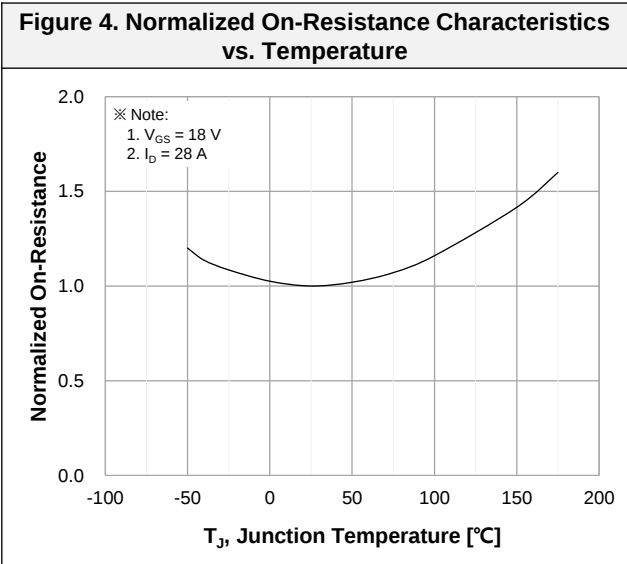
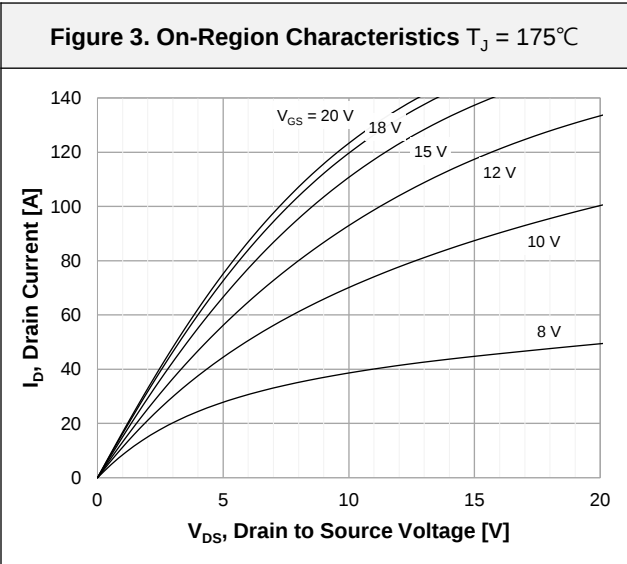
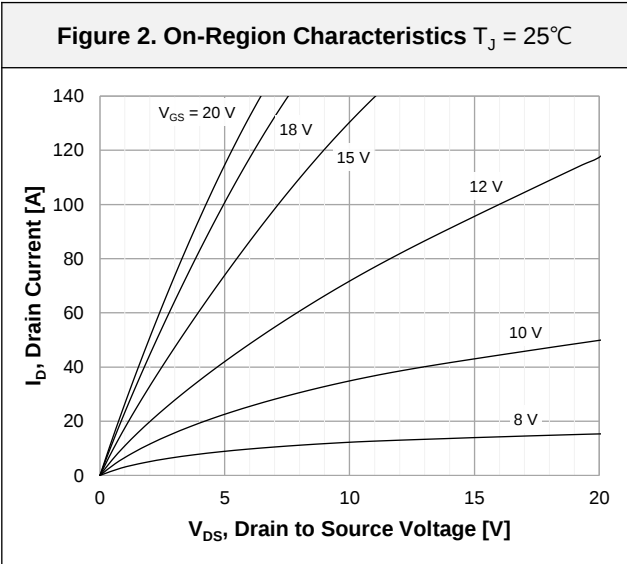
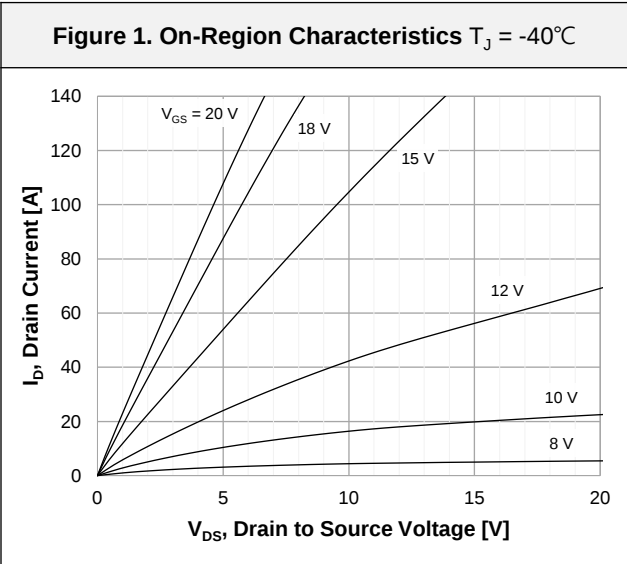
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 800\text{ V}, I_D = 28\text{ A},$ $V_{GS} = -3\text{ V} / 18\text{ V}, R_G = 6.8\text{ }\Omega,$ FWD : HCH120S20D1, Inductive load		19		ns
t_r	Turn-On Rise Time			15		
$t_{d(off)}$	Turn-Off Delay Time			35		
t_f	Turn-Off Fall Time			8		
E_{on}	Turn-on Switching Energy			158		μJ
E_{off}	Turn-off Switching Energy			100		
E_{tot}	Total Switching Energy			258		

Electrical Characteristics (T_C = 25°C unless otherwise noted)

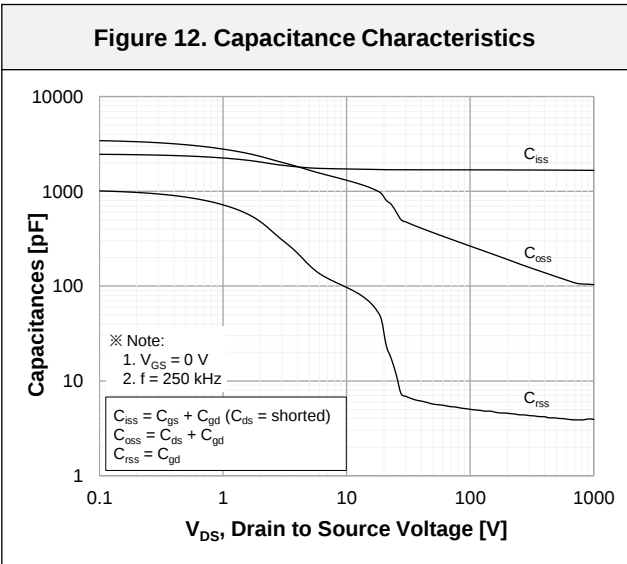
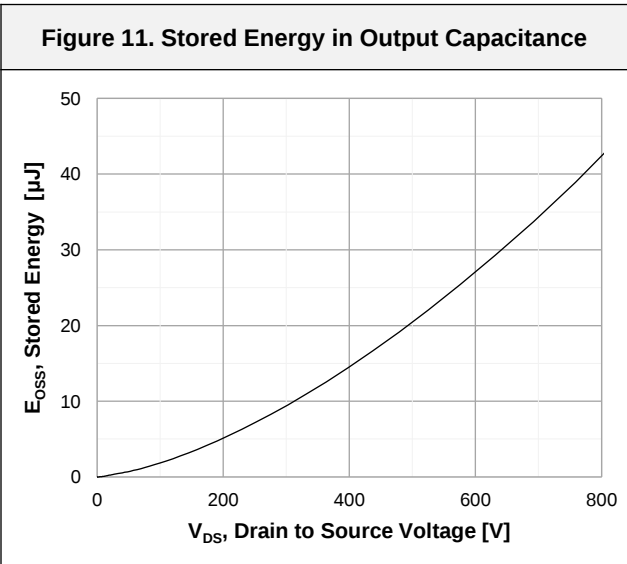
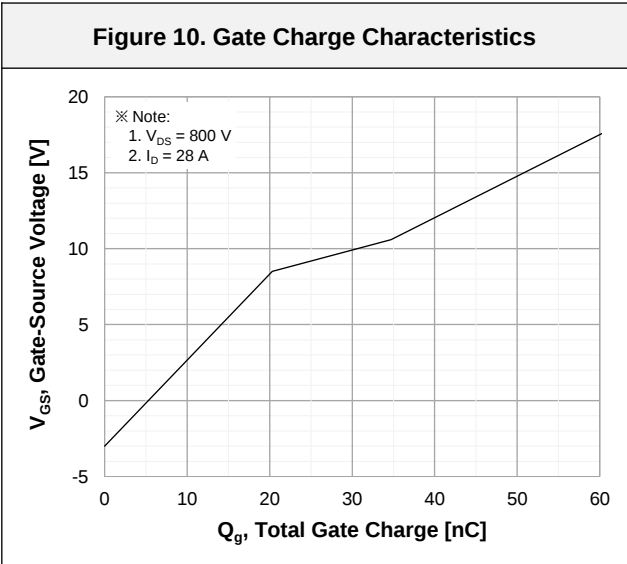
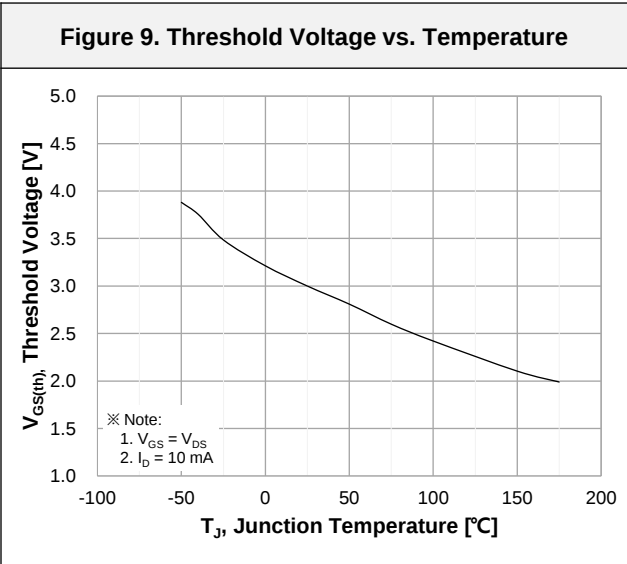
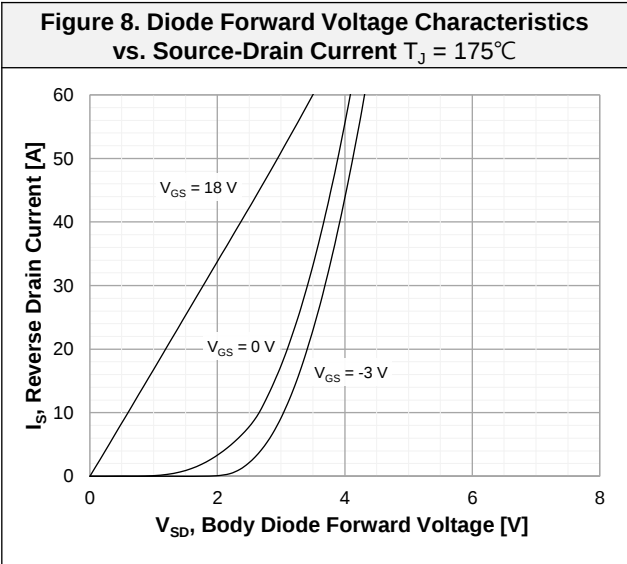
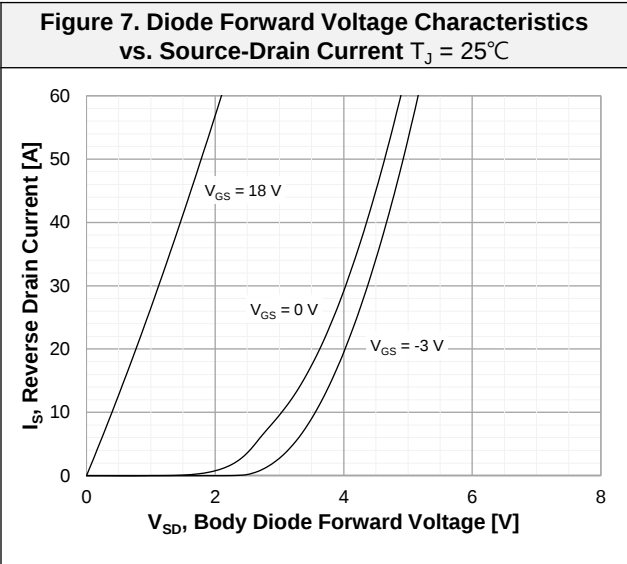
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Source-Drain Diode Characteristics						
I _S	Continuous Diode Forward Current	V _{GS} = -3 V			57	A
I _{SM}	Pulsed Diode Forward Current	V _{GS} = -3 V (Note1)			142	
V _{SD}	Diode Forward Voltage	V _{GS} = -3 V, I _{SD} = 28 A		4.3		V
t _{rr}	Reverse Recovery Time	V _{DD} = 800 V, I _{SD} = 28 A, dI _F /dt = 3000 A/μs, Includes Q _{oss}		15		ns
Q _{rr}	Reverse Recovery Charge			219		nC
I _{rrm}	Peak Reverse Recovery Current			24		A

※Note 1 : Limited by maximum junction temperature.
※Note 2 : DBC discoloration and Picker Circle Printing allowed.

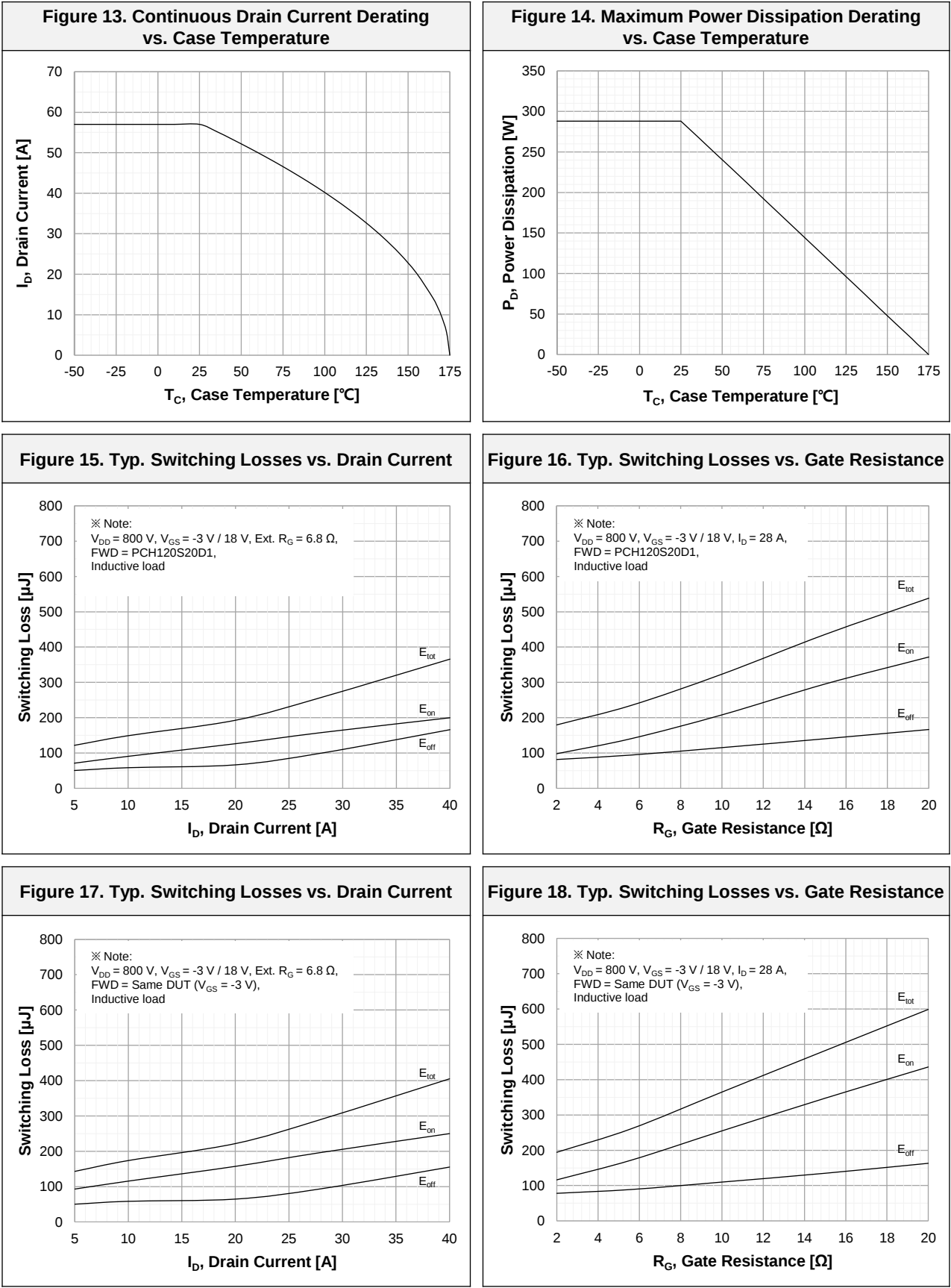
Typical Performance Characteristics



Typical Performance Characteristics



Typical Performance Characteristics



Typical Performance Characteristics

Figure 19. Maximum Safe Operating Area

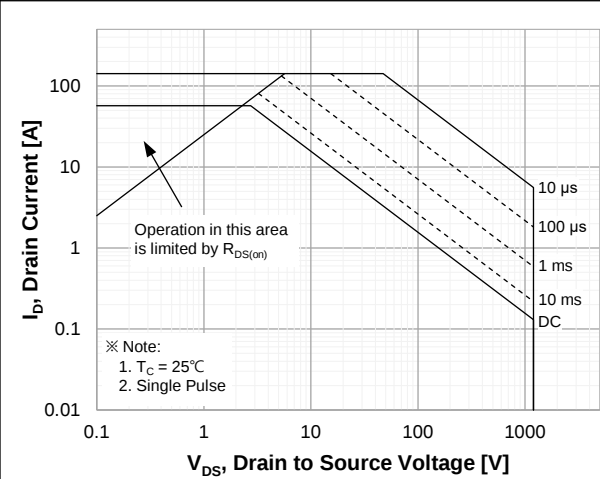


Figure 20. Transient Thermal Response Curve

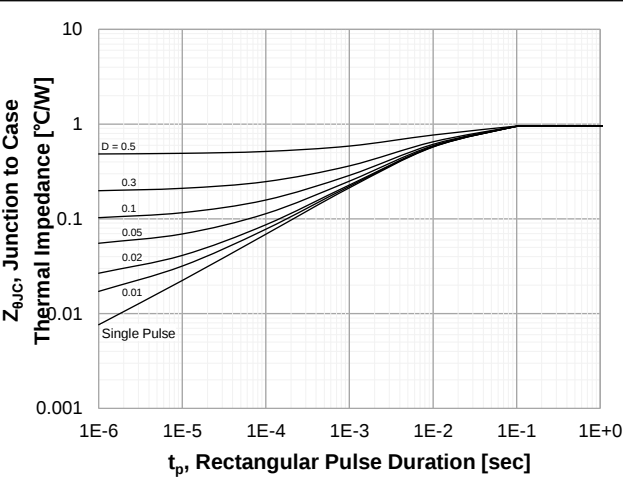


Figure 21. Inductive Load Switching Test Circuit and Waveforms

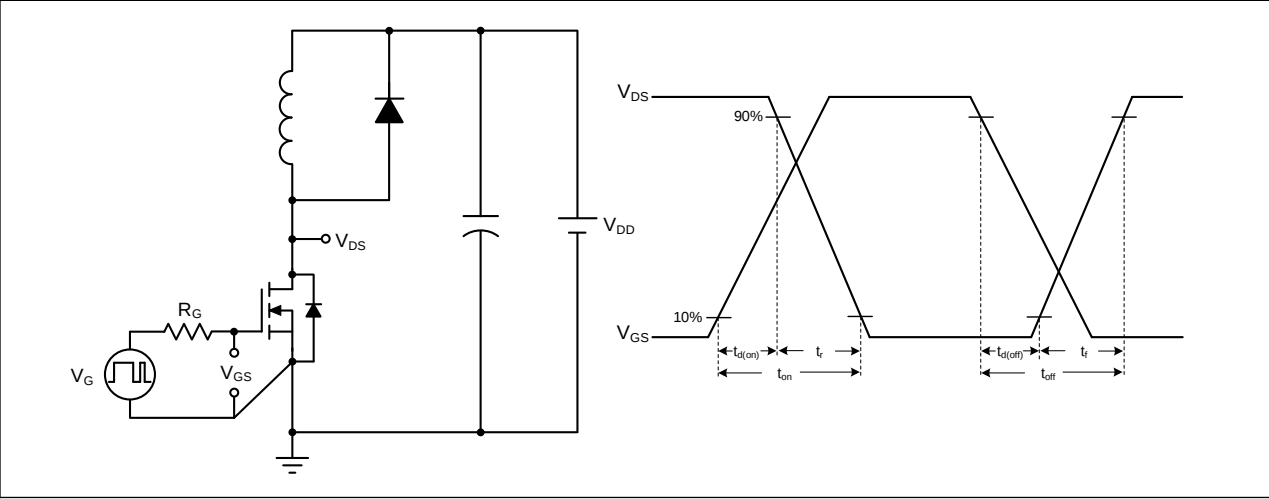
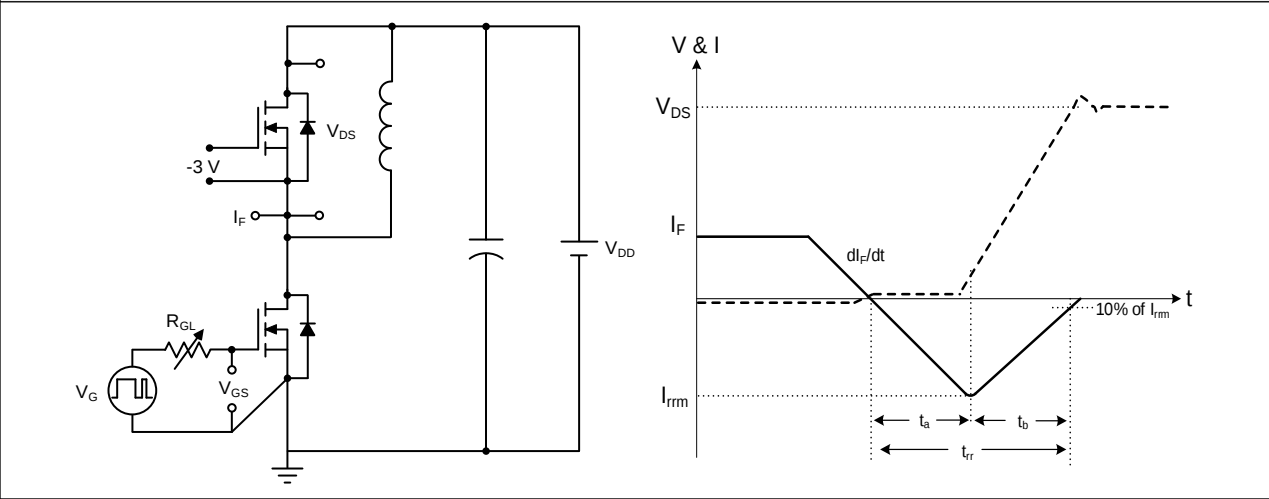
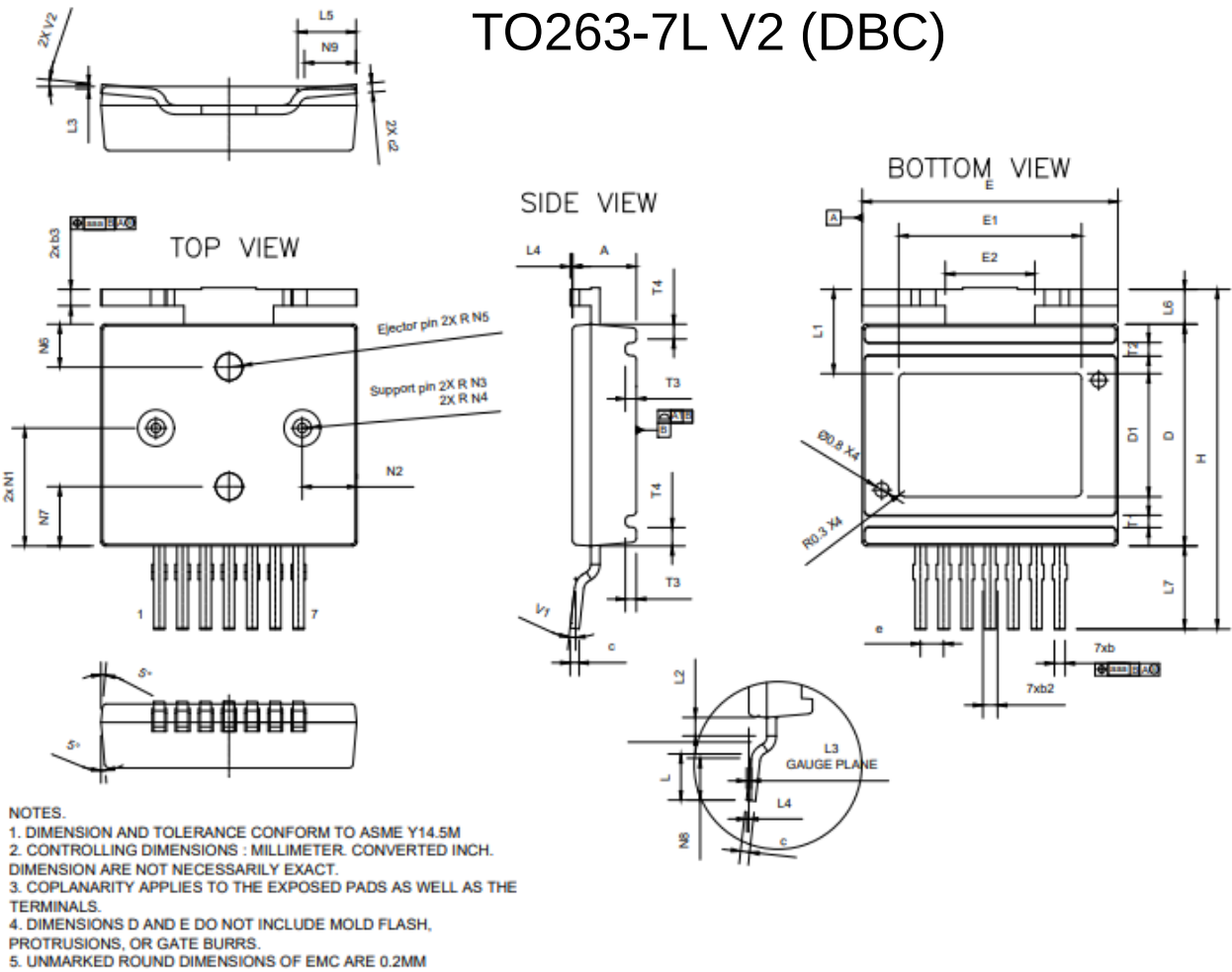


Figure 22. Peak Diode Recovery dv/dt Test Circuit and Waveforms

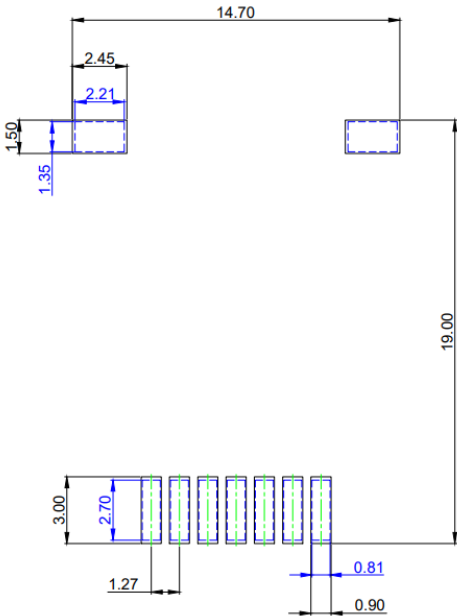


Package Outlines

TO263-7L V2 (DBC)



[Footprint guide]



Package Outlines

SYMBOL	Common		
	DIMENSIONS MILLIMETER		
	MIN.	NOM.	MAX.
A	3.40	3.50	3.60
A1	0.05		
b	0.50	0.60	0.70
b2	0.70	0.80	0.90
b3	0.80	0.90	0.98
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	12.04	12.14	12.24
D1	6.29	6.74	7.34
E	13.90	14.00	14.10
E1	9.55	10.00	10.60
E2	4.85	4.90	4.95
e	1.27		
H	18.00	18.58	19.00
L	2.42	2.52	2.62
L1	4.60		
L2	0.90	1.00	1.10
L3	0.26		
L4	0.075	0.125	0.175
L5	3.09	3.19	3.29
L6	1.80	1.90	2.00
L7	4.44	4.54	4.64
N1	6.35	6.45	6.55
N2	2.95	3.00	3.05
N3	0.40	0.50	0.60
N4	0.20	0.25	0.30
N5	0.65	0.75	0.85
N6	2.25	2.35	2.45
N7	3.15	3.25	3.35
N8	2.185	2.285	2.385
N9	2.73	2.83	2.93
V1	0°	5°	8°
V2	0°	6°	8°
T1	0.69		
T2	0.74		
T3	0.60		
T4	1.00		
aaa	0.10		